

N-channel TrenchMOS intermediate level FET

Rev. 2 — 21 September 2010

Product data sheet

1. Product profile

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources

1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoids

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1.	Quick reference data	3
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	-	50	A
P _{tot}	total power dissipation	see <u>Figure 2</u>		-	-	80	W
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 12 A; T _{mb} = 25 °C; see <u>Figure 11</u>		-	9.5	11.2	mΩ



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Table 1.	Quick reference da	tacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 50 \text{ A}; \ V_{sup} \leq 40 \text{ V}; \\ V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \\ \text{unclamped} \end{array}$	-	-	55	mJ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$\label{eq:ID} \begin{array}{l} I_D = 25 \text{ A}; \ V_{DS} = 32 \text{ V}; \\ V_{GS} = 10 \text{ V}; \text{ see } \underline{Figure \ 13}; \\ \text{see } \underline{Figure \ 14} \end{array}$	-	10.1	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

3. Ordering information

Table 3. Ordering information	Table 3.	Orderina	information
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Type number	Package		
	Name	Description	Version
BUK6212-40C	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage	Pulsed	<u>[1]</u>	-20	20	V
		DC	[2]	-16	16	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 1}}$	[3]	-	50	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1		-	41	А
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see <u>Figure 3</u>		-	233	А
P _{tot}	total power dissipation	see Figure 2		-	80	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I _S	source current	T _{mb} = 25 °C	[3]	-	50	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	233	А
Avalanche r	uggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ I_D = 50 \text{ A}; \text{V}_{\text{sup}} \leq 40 \text{ V}; \text{V}_{\text{GS}} = 10 \text{ V}; \\ \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} $		-	55	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		<u>[4][5][6]</u>	-	-	J

[1] Accumulated pulse duration not to exceed 5 minutes.

[2] -16V accumulated duration not to exceed 168 hrs.

[3] Continuous current is limited by package.

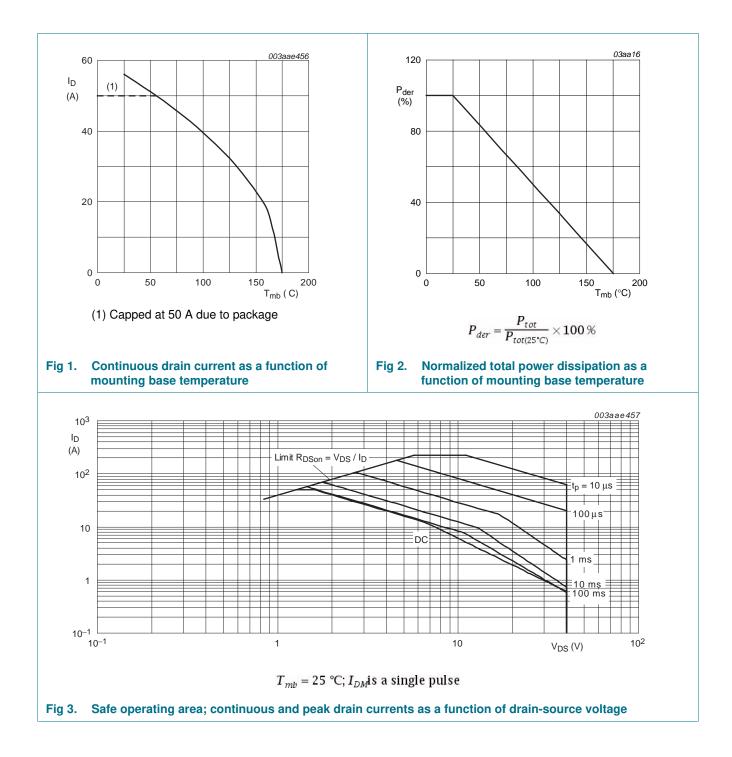
[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[6] Refer to application note AN10273 for further information.

BUK6212-40C

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5. Thermal characteristics

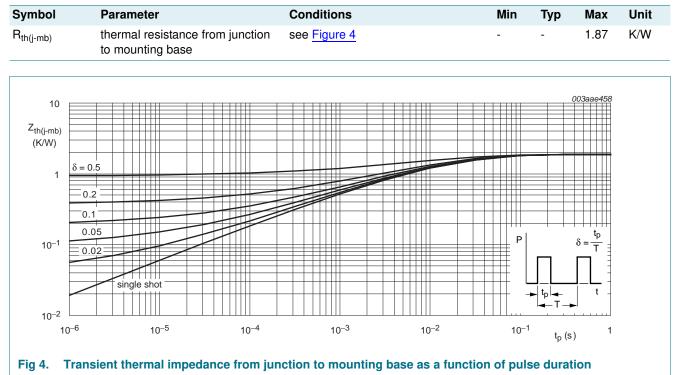


Table 5.Thermal characteristics

6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	-	-	3.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	0.8	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; \text{ V}_{GS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; \text{ V}_{GS} = -20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	2	100	nA
R _{DSon} drain-source on-state resistance	V _{GS} = 10 V; I _D = 12 A; T _{mb} = 25 °C; see <u>Figure 11</u>	-	9.5	11.2	mΩ	
	V _{GS} = 5 V; I _D = 12 A; T _j = 25 °C; see <u>Figure 11</u>	-	13	16.3	mΩ	
	V _{GS} = 4.5 V; I _D = 12 A; T _{mb} = 25 °C; see <u>Figure 11</u>	-	15	20	mΩ	
		V _{GS} = 10 V; I _D = 12 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	-	23.5	mΩ
Dynamic ch	aracteristics					
Q _{G(tot)} total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	33.9	-	nC	
		$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	19.5	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	5.4	-	nC
Q _{GD}	gate-drain charge	see Figure 13; see Figure 14	-	10.1	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1422	1900	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 15}{15}$	-	205	250	pF
C _{rss}	reverse transfer capacitance		-	143	200	pF
d(on)	turn-on delay time	$V_{DS} = 30 \ V; \ R_L = 1.2 \ \Omega; \ V_{GS} = 10 \ V;$	-	9.7	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega$	-	21	-	ns
d(off)	turn-off delay time		-	54	-	ns
l _f	fall time		-	32	-	ns
LD	internal drain inductance	measured from source lead to source bond pad; ; $T_j = 25 \text{ °C}$	-	3.5	-	nH
L _S	internal source inductance	$T_j = 25 \text{ °C}$; measured from drain to centre of die;	-	2.5	-	nH

Symbol

BUK6212-40C

Max

Unit

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Тур

Min

ource-drai	n diode						
SD	source-drain voltage	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V};$ see Figure 16	T _j = 25 °C;	-	0.9	1.2	V
	reverse recovery time	$I_{\rm S} = 20 \text{ A}; dI_{\rm S}/dt = -10$	$00 \text{ A}/\mu\text{s}; \text{V}_{\text{GS}} = 0 \text{ V};$	-	35.6	-	ns
r	recovered charge	V _{DS} = 25 V		-	38	-	nC
100 I _D (A) 80 60 40 20 0 0	V _{GS} (V) = 10 8	003aae459 5 4.5 4.5 4.5 4.5 4.5 4.5 4.5 4.5 4.5 4	$\begin{array}{c} 60\\ g_{fs}\\ (S)\\ 40\\ 20\\ 0\\ 0\\ 0\\ 0\\ 10 \end{array}$	20	30	203aae461	
	$T_j = 25$ °C; $t_p = 300$	μs current as a	T_j Fig 6. Forward trans		= 25 V nce as a	I _D (A)	n of
	v. ₩ 3. 62° ¥3. •	μs n current as a	T_{j}	nsconducta	= 25 V nce as a		n of
fun	tput characteristics: drair	μs n current as a	<i>T_j</i> Fig 6. Forward trandrain current	nsconducta	= 25 V nce as a lues		n of
	tput characteristics: drair	μs n current as a age; typical values	T_j Fig 6. Forward trans	nsconducta	= 25 V nce as a lues	functio	n of
60 I _D (A)	tput characteristics: drain action of drain-source volt	μs n current as a age; typical values	T_{j} Fig 6. Forward trandrain current $\begin{pmatrix} 40 \\ R_{DSon} \\ (m\Omega) \\ 30 \end{pmatrix}$	nsconducta	= 25 V nce as a lues	functio	n of
fun 60 ID (A) 40 20 0	tput characteristics: drain faction of drain-source volt $T_j = 175 \circ C$ $T_j = 1000$	μs age; typical values	T_j Fig.6. Forward tran drain current (m_2) 30 20 10 0 0 5	nsconductar at; typical va	= 25 V nce as a lues		n of

Table 6. Characteristics ...continued

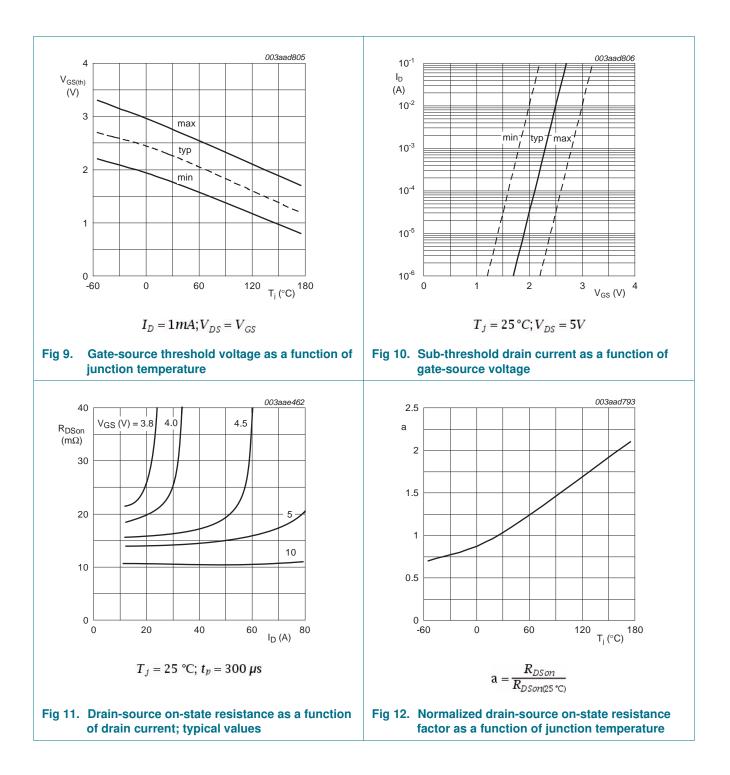
Parameter

Conditions

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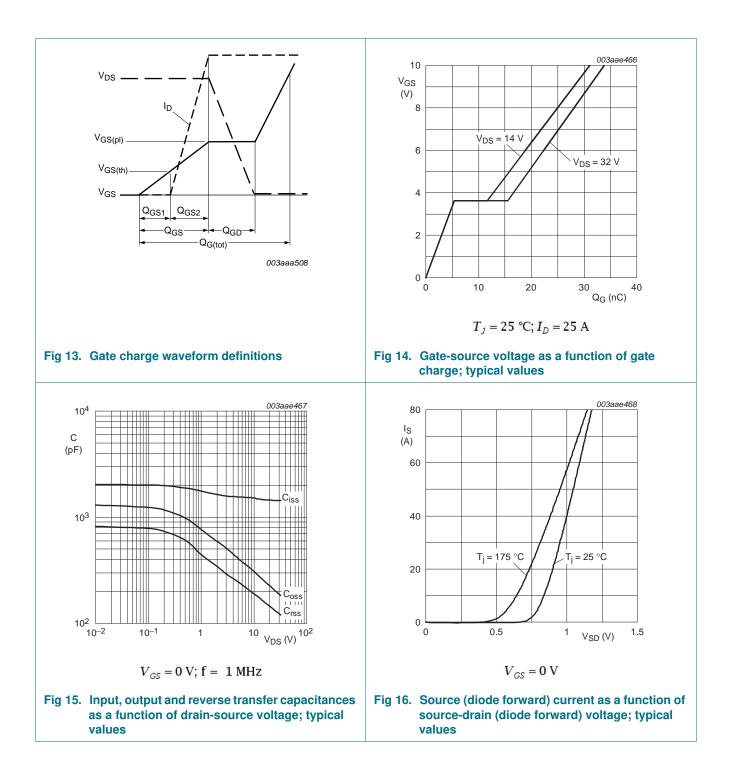
BUK6212-40C

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7. Package outline

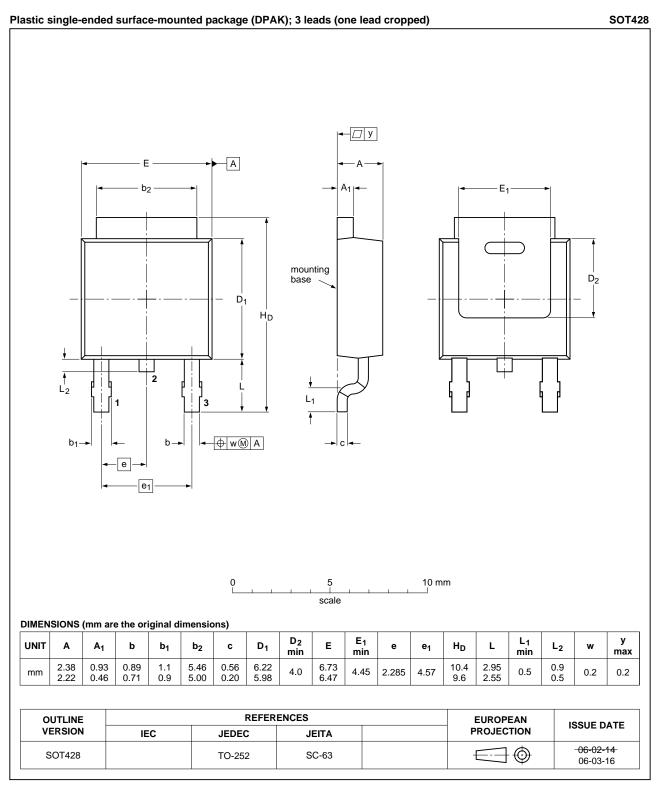


Fig 17. Package outline SOT428 (DPAK)

BUK6212-40C Product data sheet

8. Revision history

Table 7. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK6212-40C v.2	20100921	Product data sheet	-	BUK6212-40C v.1
Modifications:	Status changeVarious chang	d from Objective to Product. es to content.		
BUK6212-40C v.1	20100512	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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